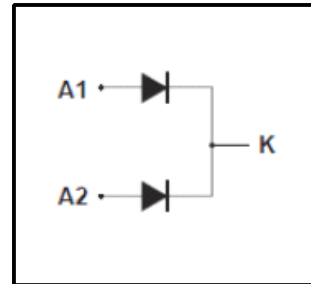


Silicon Controlled Rectifiers

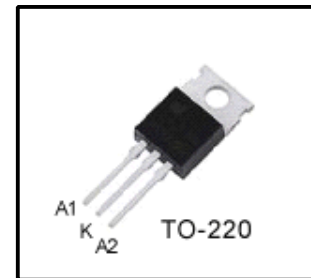
Features

- 10A(2×5A),150V
- $V_{F(max)}=0.72V(@T_J=125^{\circ}C)$
- Low power loss,high efficiency
- Common cathode structure
- Guard ring for over voltage protection, High reliability
- Maximum Junction Temperature Range($175^{\circ}C$)



General Description

Dual center tap Schottky rectifiers suited for High frequency switch power supply and Free wheeling diodes, polarity protection applications.



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{DRM}	Repetitive Peak reverse Voltage	150	V
V_{DC}	Maximum DC blocking Voltage	150	V
$I_{F(RMS)}$	RMS forward Current	10	A
$I_{F(AV)}$	Average forward current	Per diode	5
		Per device	10
I_{FSM}	Surge non repetitive forward current	150	A
I_{RRM}	Repetitive peak reverse current	1	A
dv/dt	Critical rate of rise of reverse voltage	10000	V/ns
T_J	Junction Temperature	175	$^{\circ}C$
T_{STG}	Storage Temperature	-40~150	$^{\circ}C$

Thermal Characteristics

Symbol	Parameter	Value			Units
		Min	Typ	Max	
R_{QJC}	Thermal Resistance Junction to Case	-	-	2.2	$^{\circ}C/W$

Electrical Characteristics (per diode)

Characteristics	Symbol	Test Conditions		Min	Typ	Max	Units
Reverse leakage current	I _R	V _R =V _{RRM}	T _j =25℃	-	-	10	μA
			T _j =125℃	-	-	4.5	mA
Forward voltage drop	V _F	I _F =5A	T _j =25℃	-	0.81	0.9	V
			T _j =125℃	-	0.67	0.72	
		I _F =10A	T _j =25℃	-	0.89	0.95	
			T _j =125℃	-	0.76	0.8	

*Notes:tp =380μs, δ<2%

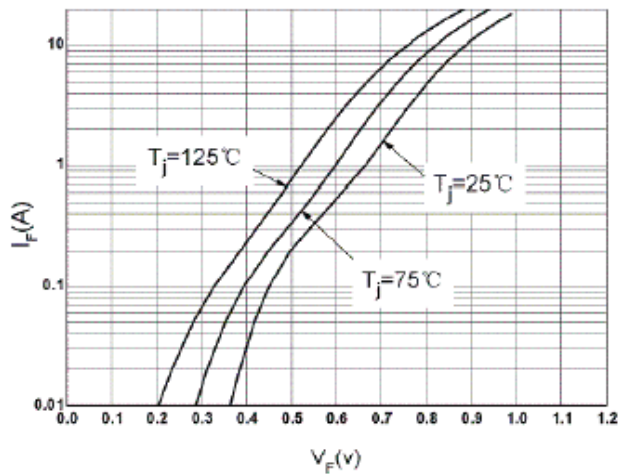


Fig.1 Forward Voltage Drop Versus Forward current (maximum Values ,per diode)

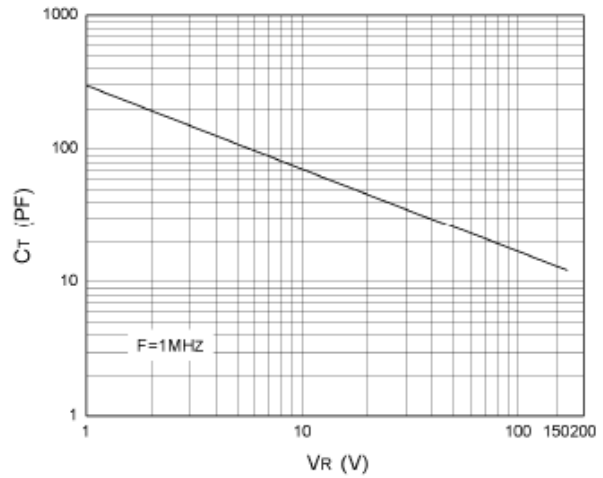


Fig .2 Junction Capacitance Versus reverse Voltage applied (typical Values,per diode)

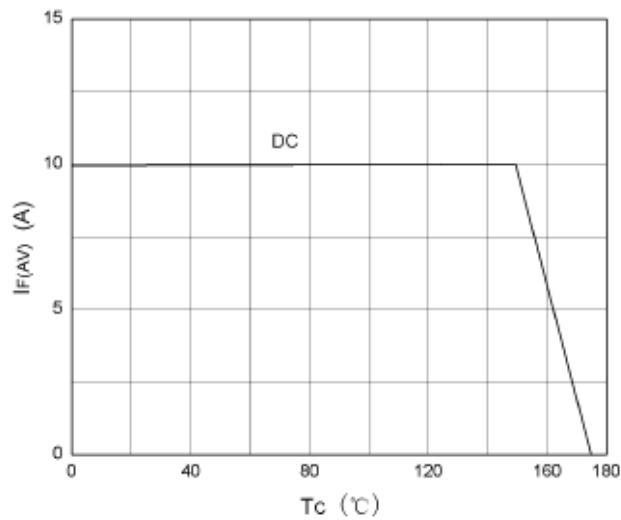


Fig. 3 Average Current versus ambient temperature (d=0.5)(per diode)

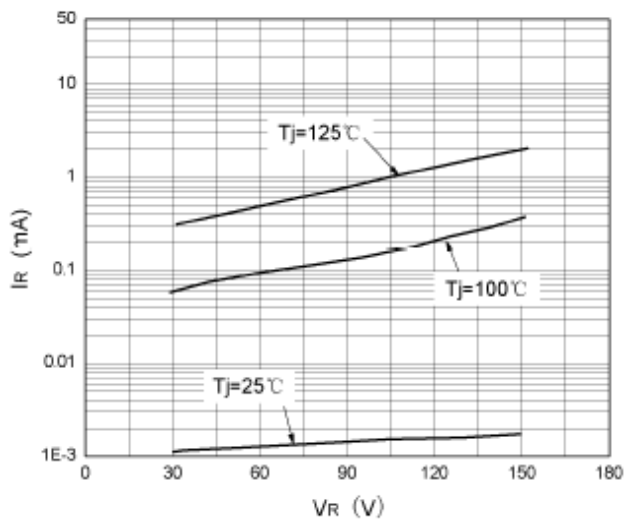


Fig. 4 Reverse leakage current versus reverse voltage applied (typical values,per diode)

TO-220 Package Dimension

